

General Description

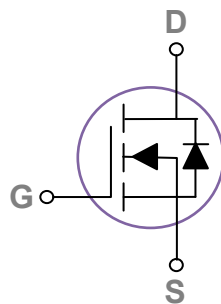
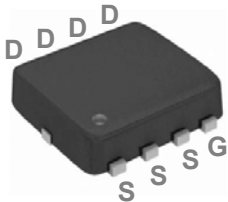
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R _{DS(ON)}	I _D
20V	3.5mΩ	80A

Features

- 20V,80A, R_{DS(ON)} =3.5mΩ@V_{GS} = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

PPAK3x3 Pin Configuration



Applications

- MB / VGA / V_{core}
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings T_c=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	± 12	V
I _D	Drain Current – Continuous (Chip Limitation ,T _C =25°C)	80	A
	Drain Current – Continuous (Chip Limitation ,T _C =100°C)	51	A
I _{DM}	Drain Current – Pulsed ¹	320	A
P _D	Power Dissipation (T _C =25°C)	66	W
	Power Dissipation – Derate above 25°C	0.53	W/°C
T _{STG}	Storage Temperature Range	-55 to 175	°C
T _J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C/W
R _{θJC}	Thermal Resistance Junction to Case	---	2	°C/W

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)
Static State Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=15A$	---	2.8	3.5	$m\Omega$
		$V_{GS}=2.5V, I_D=10A$	---	3.5	4.5	$m\Omega$
		$V_{GS}=1.8V, I_D=6A$	---	5	7	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	0.3	0.65	1	V
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=5A$	---	35	---	S

Dynamic Characteristics

Q_g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V, I_D=5A$	---	52	100	nC
Q_{gs}	Gate-Source Charge		---	6.6	12	
Q_{gd}	Gate-Drain Charge		---	13.8	28	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V, V_{GS}=4.5V, R_G=3.3\Omega$ $I_D=1A$	---	20.2	40	ns
T_r	Rise Time		---	31.2	60	
$T_{d(off)}$	Turn-Off Delay Time		---	68.5	120	
T_f	Fall Time		---	21.2	42	
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, F=1\text{MHz}$	---	3870	5500	pF
C_{oss}	Output Capacitance		---	580	850	
C_{rss}	Reverse Transfer Capacitance		---	340	600	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.3	2.6	Ω

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	80	A
I_{SM}	Pulsed Source Current ²		---	---	160	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=1A, di/dt=100A/\mu s$ $T_J=25^\circ\text{C}$	---	---	---	ns
Q_{rr}	Reverse Recovery Charge		---	---	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

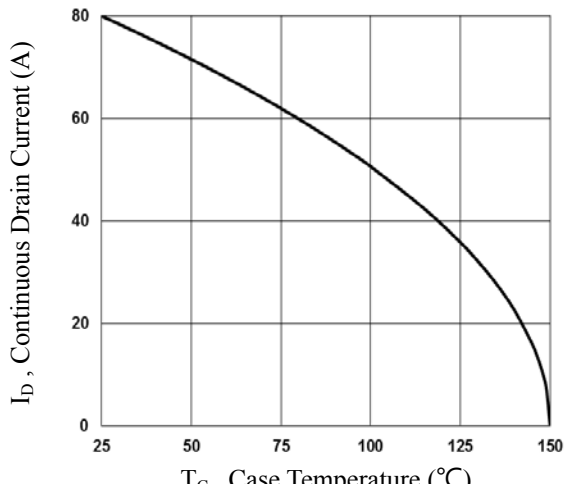


Fig.1 Continuous Drain Current vs. T_c

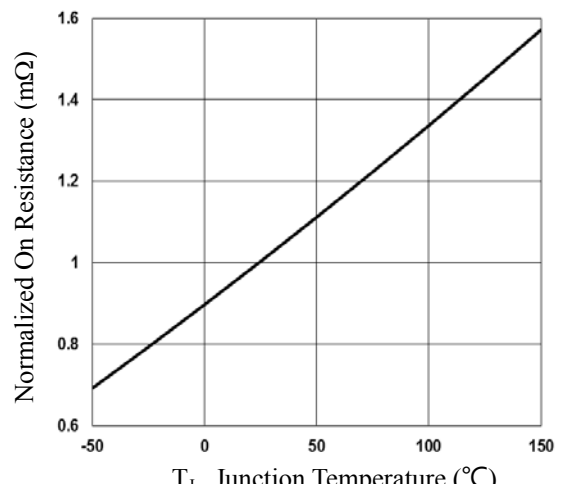


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

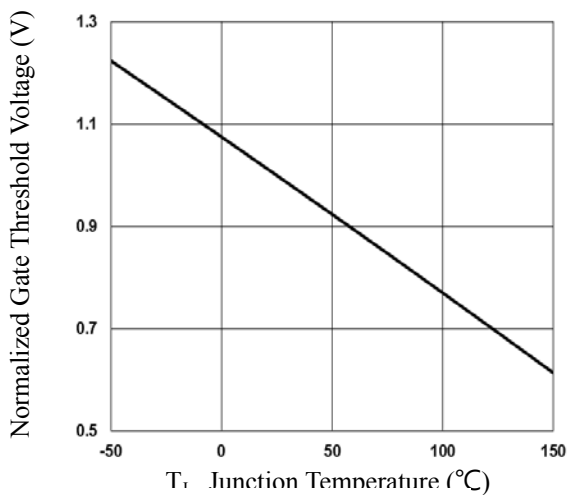


Fig.3 Normalized V_{th} vs. T_j

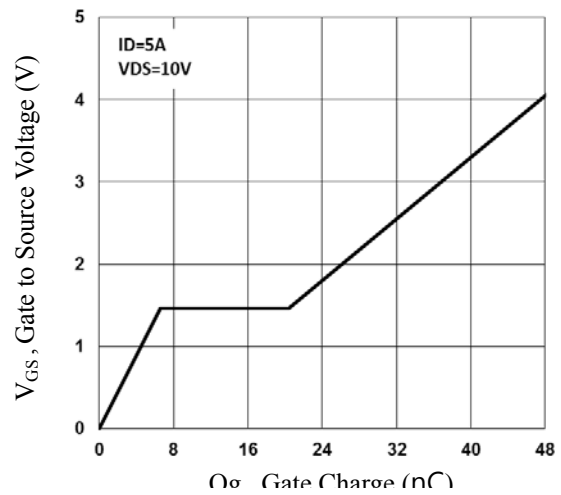


Fig.4 Gate Charge Waveform

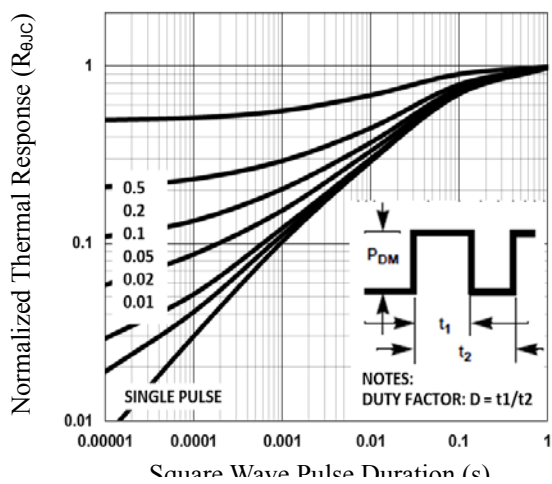


Fig.5 Normalized Transient Impedance

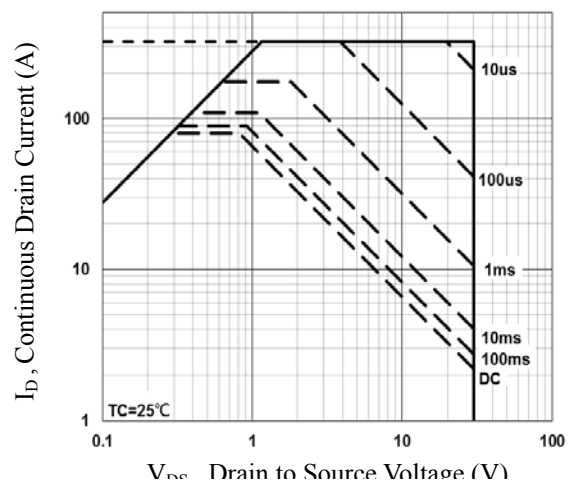


Fig.6 Maximum Safe Operation Area

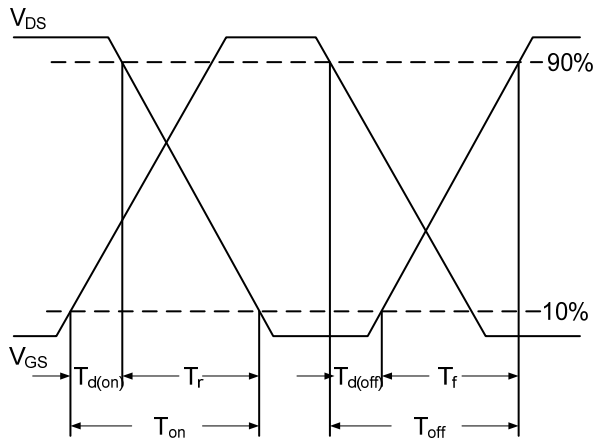


Fig.7 Switching Time Waveform

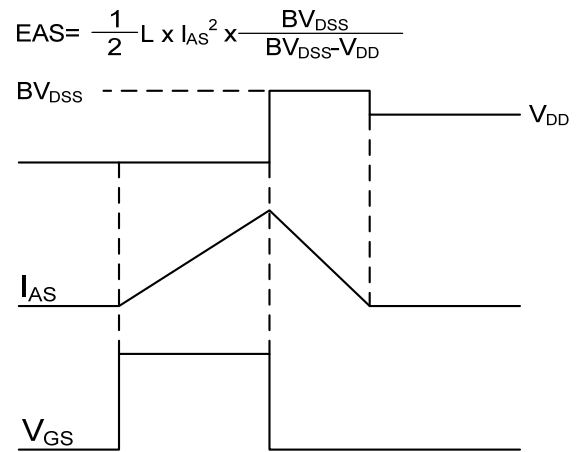
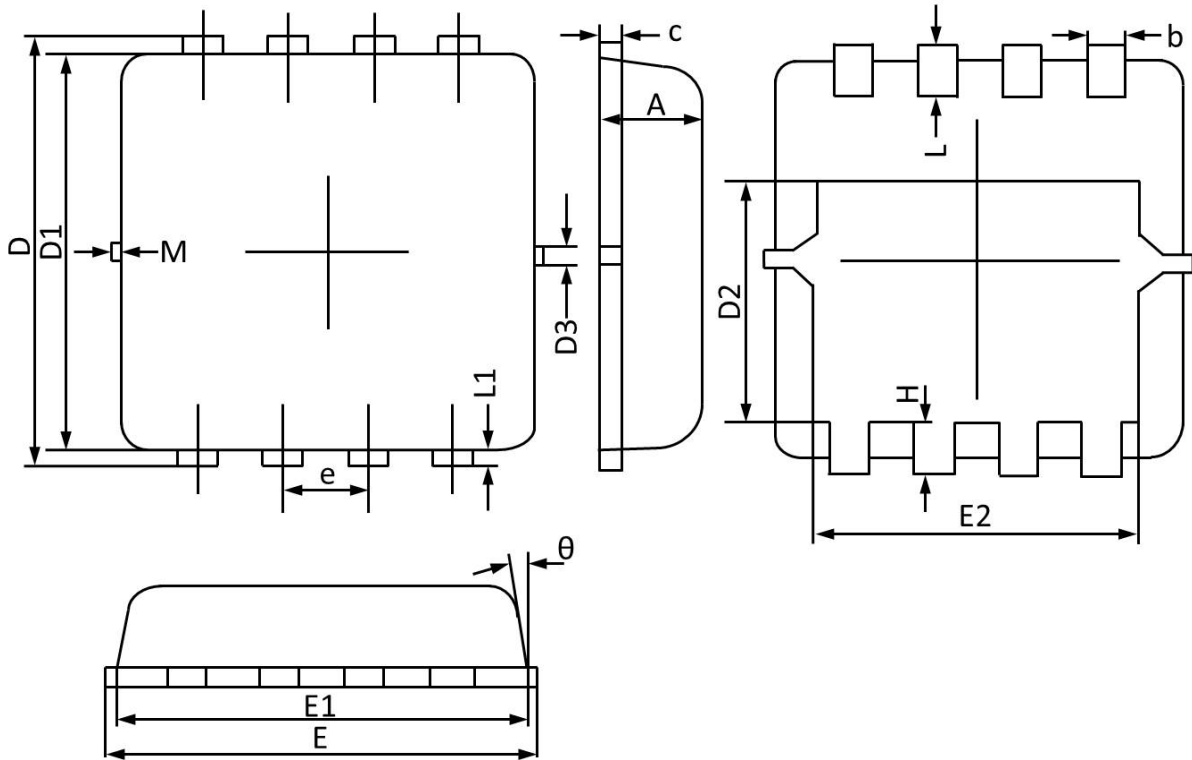


Fig.8 EAS Waveform

PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	